

Search Results				
Type	L #	Hits	Search Text	DBs
1 BRS	L1	5	memory with ((back adj gate) near5 (potential or bias or volt\$3)) with writ\$3 with read\$3	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
2 BRS	L2	1	memory with substrate with (potential or bias or volt\$3) with chang\$3 with (back adj gate) with response with mode with operat\$3	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
3 BRS	L3	1	memory with substrate with (potential or bias or volt\$3) with chang\$3 with (back adj gate) and (response with mode with operat\$3)	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
4 BRS	L4	83	memory with substrate with (potential or bias or volt\$3) and chang\$3 and (back adj gate) and (response with mode with operat\$3)	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
5 BRS	L5	12	memory with substrate with (potential or bias or volt\$3) and (chang\$3 with (back adj gate)) and (response with mode with operat\$3)	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

**Ready**

**EAST - [default.wsp:1]**

File View Edit Tools Window Help

Drafts Pending Active L8: (315) memory with ((back adj gate) or substrate  
L10: (50) 9 and (potential or bias or volt\$3)  
L9: (68) 8 and (operat\$3 near3 mode)

Failed Saved Favorites Tagged (5) UDC Queue Trash

Search List Browse Queue Clear

DBs US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM\_TDB

Default operator: OR  Plural  Highlight all hit terms initially

BRS form IS4R form Image Text HTML

	Type	L #	Hits	Search Text	DBs
1	BRS	L8	315	memory with ((back adj gate) or substrate or channel or body) with (chang\$3 or vary\$3) with read\$3 with writ\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L10	50	9 and (potential or bias or volt\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L9	68	8 and (operat\$3 near3 mode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

Hits Details HTML

Ready